

LM733/LM733C Differential Amplifier

General Description

The LM733/LM733C is a two-stage, differential input, differential output, wide-band video amplifier. The use of internal series-shunt feedback gives wide bandwidth with low phase distortion and high gain stability. Emitter-follower outputs provide a high current drive, low impedance capability. Its 120 MHz bandwidth and selectable gains of 10, 100 and 400, without need for frequency compensation, make it a very useful circuit for memory element drivers, pulse amplifiers, and wide band linear gain stages.

The LM733 is specified for operation over the -55° C to $+125^{\circ}$ C military temperature range. The LM733C is specified for operation over the 0° C to $+70^{\circ}$ C temperature range.

Features

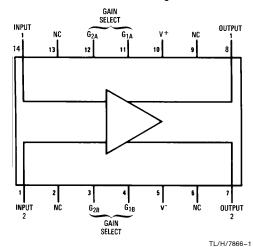
- 120 MHz bandwidth
- 250 kΩ input resistance
- Selectable gains of 10, 100, 400
- No frequency compensation
- High common mode rejection ratio at high frequencies

Applications

- Magnetic tape systems
- Disk file memories
- Thin and thick film memories
- Woven and plated wire memories
- Wide band video amplifiers

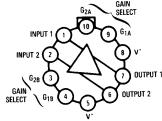
Connection Diagrams

Dual-In-Line Package



Top View Order Number LM733CN See NS Package Number N14A

Metal Can Package



TL/H/7866-2

Top View

Order Number LM733H or LM733CH See NS Package Number H10D

Absolute Maximum Ratings

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

 Diffential Input Voltage
 ±5V

 Common Mode Input Voltage
 ±6V

 V_{CC}
 ±8V

 Output Current
 10 mA

Power Dissipation (Note 1) 500 mW Junction Temperature $+150^{\circ}\mathrm{C}$ Storage Temperature Range $-65^{\circ}\mathrm{C}$ to $+150^{\circ}\mathrm{C}$ Operating Temperature Range

Electrical Characteristics ($T_A = 25^{\circ}C$, unless otherwise specified, see test circuits, $V_S = \pm 6.0V$)

Characteristics	Test Circuit	Test Conditions	LM733			LM733C			Units
			Min	Тур	Max	Min	Тур	Max	0.1110
Differential Voltage Gain Gain 1 (Note 2) Gain 2 (Note 3) Gain 3 (Note 4)	1	$R_L = 2 k\Omega V_{OUT} = 3 Vp-p$	300 90 9.0	400 100 10	500 110 11	250 80 8.0	400 100 10	600 120 12	
Bandwidth Gain 1 Gain 2 Gain 3	2			40 90 120			40 90 120		MHz MHz MHz
Rise Time Gain 1 Gain 2 Gain 3	2	V _{OUT} = 1 Vp-p		10.5 4.5 2.5	10		10.5 4.5 2.5	12	ns ns ns
Propagation Delay Gain 1 Gain 2 Gain 3	2	V _{OUT} = 1 Vp-p		7.5 6.0 3.6	10		7.5 6.0 3.6	10	ns ns ns
Input Resistance Gain 1 Gain 2 Gain 3			20	4.0 30 250		10	4.0 30 250		kΩ kΩ kΩ
Input Capacitance		Gain 2		2.0			2.0		pF
Input Offset Current				0.4	3.0		0.4	5.0	μΑ
Input Bias Current				9.0	20		9.0	30	μΑ
Input Noise Voltage		BW = 1 kHz to 10 MHz		12			12		μVrms
Input Voltage Range	1		±1.0			±1.0			V
Common Mode Rejection Ratio Gain 2 Gain 2	1	$V_{CM}=\pm 1Vf\leq 100kHz$ $V_{CM}=\pm 1Vf=5MHz$	60	86 60		60	86 60		dB dB
Supply Voltage Rejection Ratio Gain 2	1	$\Delta V_{S} = \pm 0.5V$	50	70		50	70		dB
Output Offset Voltage Gain 1 Gain 2 and 3	1	R _L = ∞		0.6 0.35	1.5 1.0		0.6 0.35	1.5 1.5	V V
Output Common Mode Voltage	1	R _L = ∞	2.4	2.9	3.4	2.4	2.9	3.4	V
Output Voltage Swing	1	$R_L = 2k$	3.0	4.0		3.0	4.0		
Output Sink Current			2.5	3.6		2.5	3.6		mA
Output Resistance				20			20		Ω
Power Supply Current	1	R _L = ∞		18	24		18	24	mA

Electrical Characteristics (Continued)

(The following specifications apply for $-55^{\circ}C < T_A < 125^{\circ}C$ for the LM733 and $0^{\circ}C < T_A < 70^{\circ}C$ for the LM733C, $V_S = \pm 6.0V$)

Characteristics	Test Circuit	Test Conditions	LM733			LM733C			Units
			Min	Тур	Max	Min	Тур	Max	Oills
Differential Voltage Gain Gain 1 Gain 2 Gain 3	1	$R_L = 2 k\Omega, V_{OUT} = 3 Vp-p$	200 80 8.0		600 120 12.0	250 80 8.0		600 120 12.0	
Input Resistance Gain 2			8			8			kΩ
Input Offset Current					5			6	μΑ
Input Bias Current					40			40	μΑ
Input Voltage Range	1		±1			± 1			V
Common Mode Rejection Ratio Gain 2	1	$V_{CM} = \pm 1V f \le 100 \text{ kHz}$	50			50			dB
Supply Voltage Rejection Ratio Gain 2	1	$\Delta V_S = \pm 0.5 V$	50			50			dB
Output Offset Voltage Gain 1 Gain 2 and 3	1	$R_L = \infty$			1.5 1.2			1.5 1.5	V V
Output Voltage Swing	1	$R_L = 2k$	2.5			2.8			V _{pp}
Output Sink Current			2.2			2.5			mA
Power Supply Current	1	$R_L = \infty$			27			27	mA

Note 1: The maximum junction temperature of the LM733 is 150°C, while that of the LM733C is 100°C. For operation at elevated temperatures devices in the TO-100 package must be derated based on a thermal resistance of 150°C/W junction to ambient or 45°C/W junction to case. Thermal resistance of the dual-in-line package is 90°C/W.

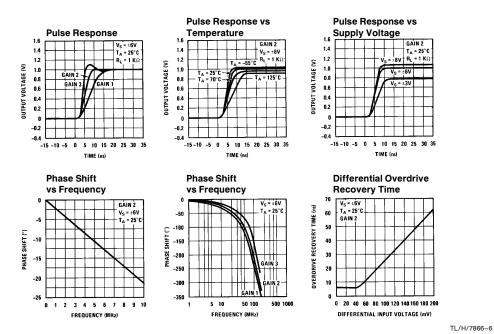
Note 2: Pins G1A and G1B connected together.

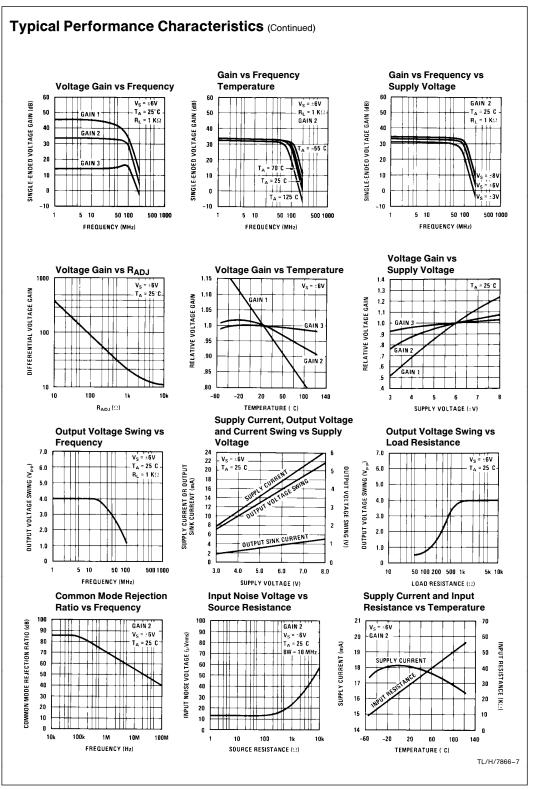
Note 3: Pins G2A and G2B connected together.

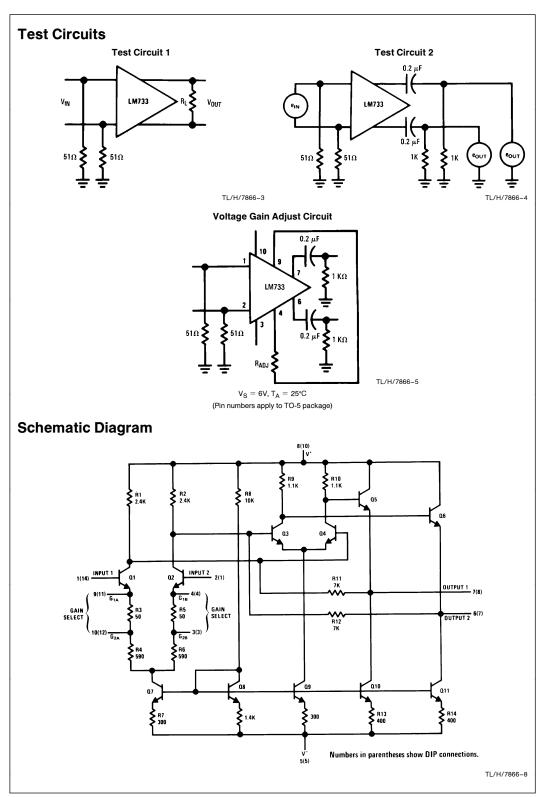
Note 4: Gain select pins open.

Note 5: Refer to RETS733X drawing for specifications of LM733H version.

Typical Performance Characteristics

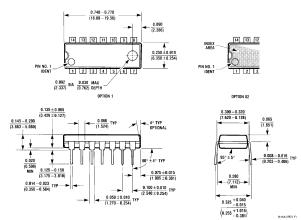






Physical Dimensions inches (millimeters) 0.350-0.370 0.315_0.335 0.240-0.260 (8.001 –8.509) (6.096-6.604) (0.889) MAX \mathbb{U} \mathbb{U} \mathbb{U} \mathbb{U} 0 500 (12.70) 0.015-0.019 (0.381-0.483) DIA TYP-0.026-0.034 (0.661-0.864) (0.737 - 1.143)Metal Can Package (H) Order Number LM733H or LM733CH

NS Package Number H10D



(5.842)

Molded Dual-In-Line Package (N) Order Number LM733CN NS Package Number N14A

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